

NIKO-SEM

N-Channel Enhancement Mode Field Effect Transistor

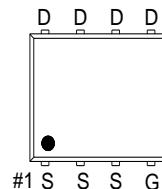
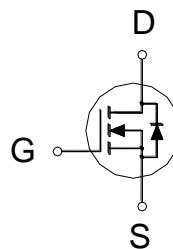
PE632BA

PDFN 3x3P

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	4.5mΩ	53A



G : GATE
D : DRAIN
S : SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ²	I_D	53	A
		33	
		21	
		17	
Pulsed Drain Current ¹	I_{DM}	100	
Avalanche Current	I_{AS}	37.5	
Avalanche Energy	E_{AS}	70	mJ
Power Dissipation	P_D	22.7	W
		9	
		3.8	
		2.4	
Operating Junction & Storage Temperature Range	T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$R_{\theta JA}$	33	63	°C/W
Junction-to-Ambient ³	Steady-State			
Junction-to-case	Steady-State			

¹Pulse width limited by maximum junction temperature.

²Package limitation current is 23A

³The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	30			V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1.3	1.7	2.3	
Gate-Body Leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 24\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
		$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 125^\circ\text{C}$			10	
Drain-Source On-State Resistance ¹	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}} = 4.5\text{V}, I_D = 15\text{A}$		4	5.5	$\text{m}\Omega$
		$V_{\text{GS}} = 10\text{V}, I_D = 15\text{A}$		3.3	4.5	
Forward Transconductance ¹	g_{fs}	$V_{\text{DS}} = 5\text{V}, I_D = 15\text{A}$		60		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 15\text{V}, f = 1\text{MHz}$		2210		pF
Output Capacitance	C_{oss}			390		
Reverse Transfer Capacitance	C_{rss}			234		
Gate Resistance	R_g	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 0\text{V}, f = 1\text{MHz}$		1.4		Ω
Total Gate Charge ²	$Q_g(V_{\text{GS}}=10\text{V})$	$V_{\text{DS}} = 15\text{V}, I_D = 15\text{A}$		44.1		nC
	$Q_g(V_{\text{GS}}=4.5\text{V})$			23		
Gate-Source Charge ²	Q_{gs}			6		
Gate-Drain Charge ²	Q_{gd}			13		
Turn-On Delay Time ²	$t_{\text{d}(\text{on})}$			25		
Rise Time ²	t_r			15		
Turn-Off Delay Time ²	$t_{\text{d}(\text{off})}$	$V_{\text{DD}} = 15\text{V}$ $I_D \approx 15\text{A}, V_{\text{GEN}} = 10\text{V}, R_G = 6\Omega$		54		nS
Fall Time ²	t_f			17		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ\text{C}$)						
Continuous Current	I_S				22.7	A
Forward Voltage ¹	V_{SD}	$I_F = 15\text{A}, V_{\text{GS}} = 0\text{V}$			1	V
Reverse Recovery Time	t_{rr}	$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		26.7		nS
Reverse Recovery Charge	Q_{rr}			12.9		nC

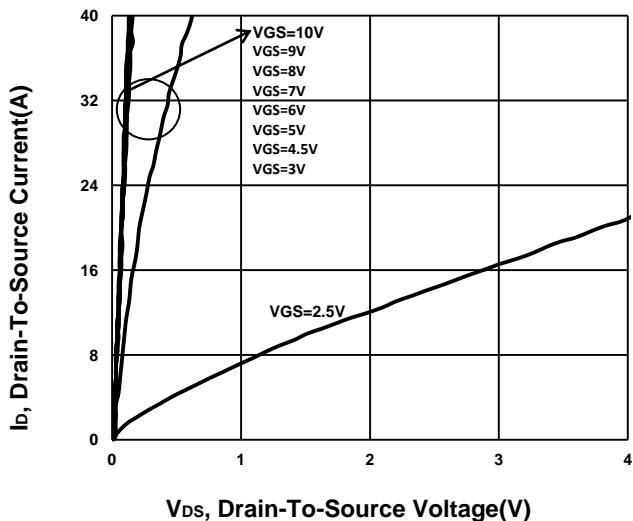
¹Pulse test : Pulse Width $\leq 300\ \mu\text{sec}$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.

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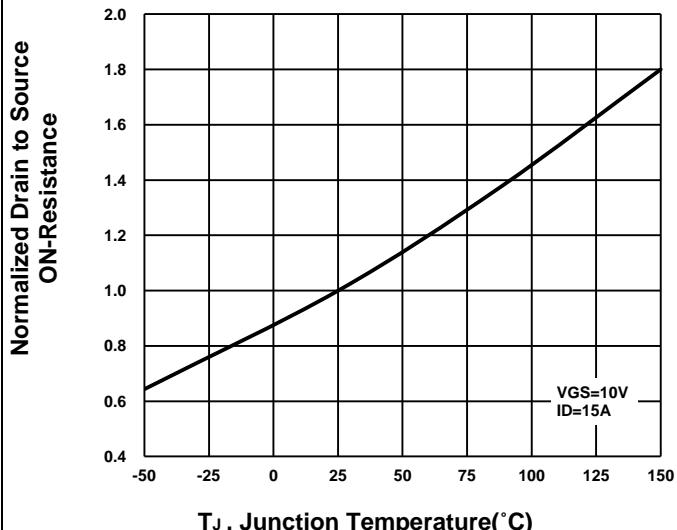
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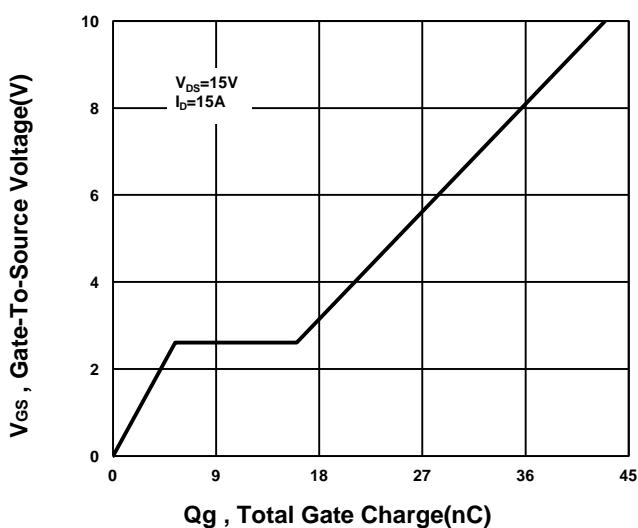
Output Characteristics



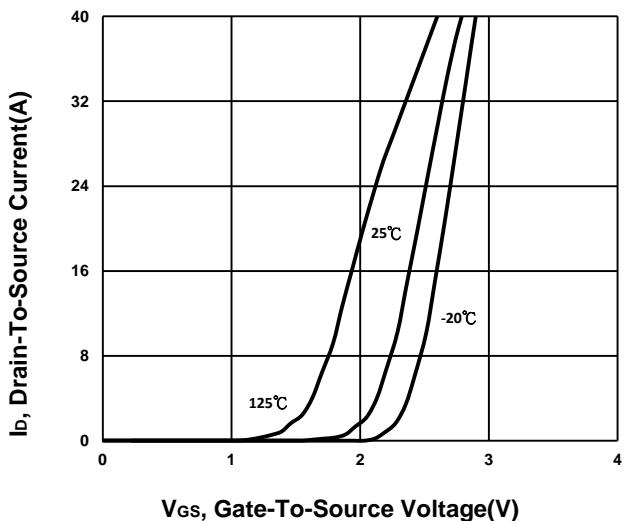
On-Resistance VS Temperature



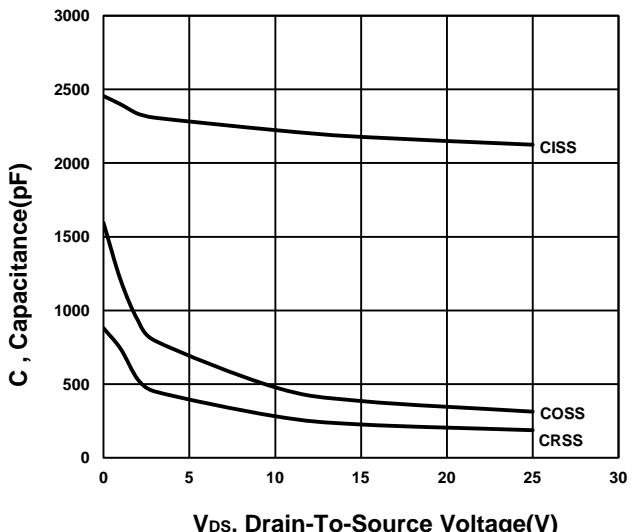
Gate charge Characteristics



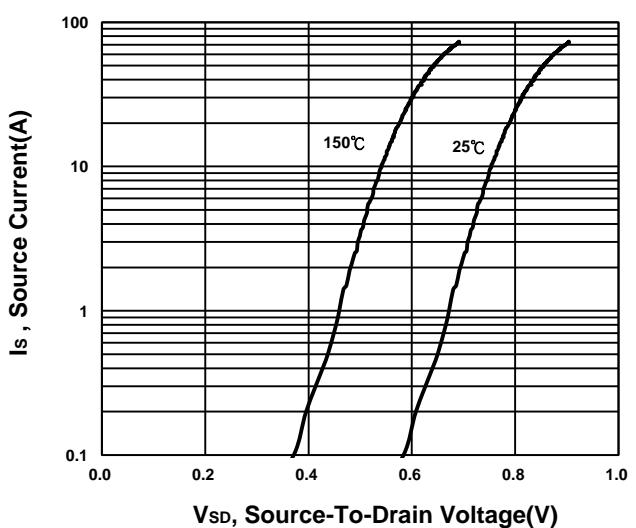
Transfer Characteristics



Capacitance Characteristic



Source-Drain Diode Forward Voltage

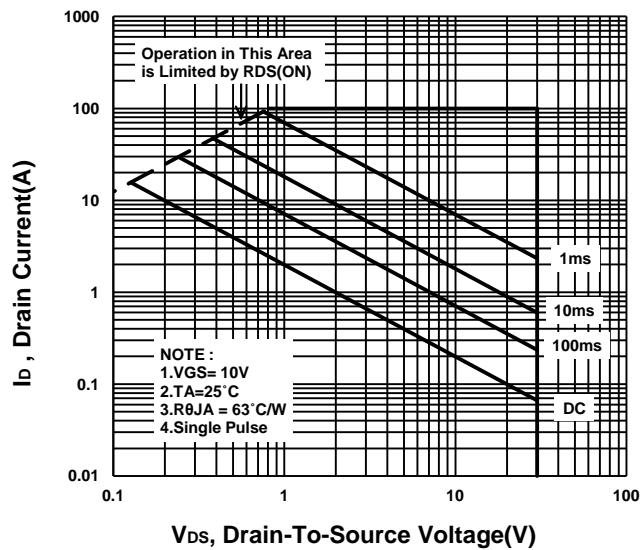


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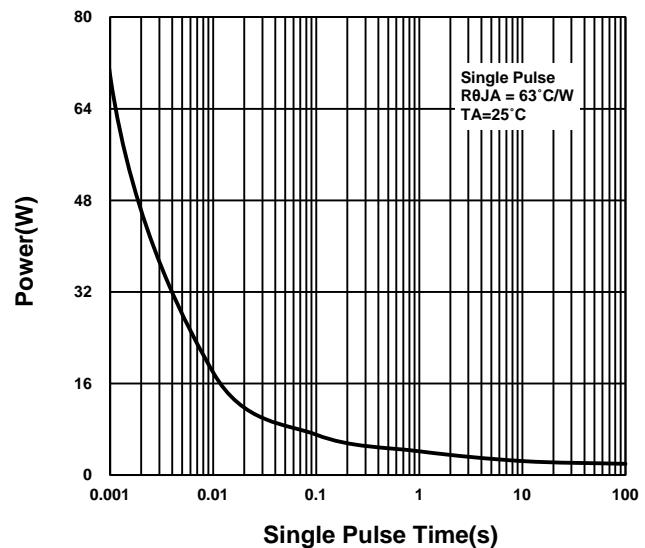
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Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

